Remarks & Arguments

In the Office Action, the Examiner noted that the Declaration of Prior Invention does not place the application in condition for allowance. The Examiner alleges that Declaration is insufficient because an explanation of how the accompanying exhibit corresponds to any of the claimed subject matter is not provided, and the exhibit does not show completion of the invention prior to the particular data. Applicants respectfully assert that one skilled in the art can fully understand the invention as claimed from the exhibit. Furthermore, the exhibit includes sufficient detail to demonstrate to one skilled in the art that the Applicants conceived and constructively reduced the claimed invention to practice. In fact, the exhibit includes the attestation of two witnesses that they understood the invention disclosed in the exhibit.

However, to assist the Examiner in more readily appreciating that the exhibit is self explanatory and demonstrates constructive reduction to practice, the Applicants have added reference numerals corresponding to Figures 3A, 3B and 4 in the application to the drawings in the attached copy of the exhibit. The independent Claims 1 and 24 are listed below are also marked-up with reference numerals corresponding to Figures 3A, 3b and 4.

1. (Original) A closed cell trench metal-oxide-semiconductor field effect transistor (TMOSFET) comprising:

a drain region (335, 340; 435, 440);

a body region (330; 430) disposed above said drain region;

a gate region (320; 420) disposed within said body region;

a gate insulator region (325; 425) disposed about a periphery of said gate region;

a plurality of source regions (315; 415) disposed along the surface of said body region proximate a periphery of said gate insulator region;

wherein a first portion of said gate region and a first portion of said gate insulator region are formed as a substantially parallel elongated structure (322; 421);

wherein a second portion of said gate region and a second portion of said gate insulator region are formed as a normal-to-parallel structure (321; 422);

wherein a first portion of said drain region overlaps said parallel structure (350; 451); and

wherein a second portion of said drain region is separated from said normal-to-parallel structure (351; 450).

24. (Original) A closed cell trench metal-oxide-semiconductor field effect transistor (TMOSFET) comprising:

a plurality of open gate-drain regions (351; 450) arranged in a first plurality of parallel regions (321; 422); and

a plurality of closed gate-drain regions (350; 451) arranged in a second plurality of parallel regions normal to said open gate-drain regions (322; 421).

From the marked-up copy of the exhibit and marked-up independent claims it is clear that the invention is sufficiently described in the exhibit to show an earlier data of invention of at least November 19, 2002.

Conclusion

For all the reasons advanced above, Applicants respectfully submit that the present application is in condition for allowance and that action is earnestly solicited. The Examiner is invited to contact Applicants' undersigned representative if the Examiner believes such action would expedite resolution of the present Application.

The Commissioner is hereby authorized to charge any additional fees, which may be required for this amendment, or credit any overpayment, to Deposit Account 23-0085. In the event that an extension of time is required, or may be required in addition to that requested in a petition for an extension of time, the Commissioner is requested to grant a petition for that extension of time which is required to make this response timely and is hereby authorized to charge any fee for such an extension of time or credit any overpayment for an extension of time to Deposit Account 23-0085.

Respectfully submitted,

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Dated: August 3, 2006

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